

isc Silicon PNP Power Transistor

TIP34C

DESCRIPTION

- DC Current Gain-
: $h_{FE} = 40(\text{Min}) @ I_C = -1\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(\text{SUS})} = -100\text{V}(\text{Min})$
- Complement to Type TIP33C

APPLICATIONS

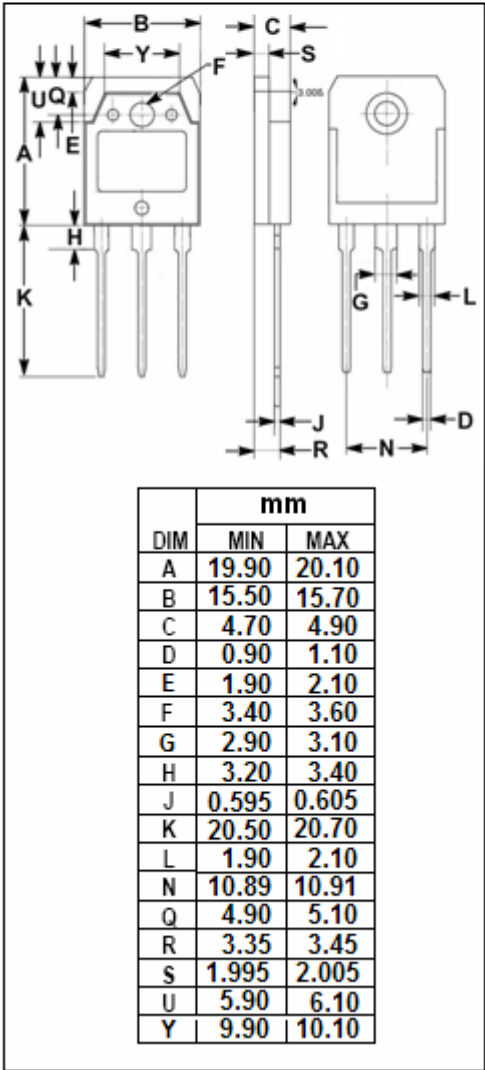
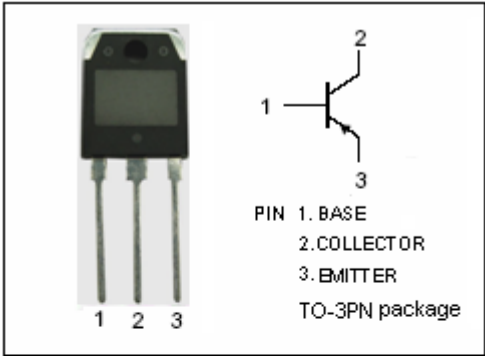
- Designed for use in general purpose power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-100	V
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-10	A
I _{CM}	Collector Current-peak	-15	A
I _B	Base Current	-3	A
P _C	Collector Power Dissipation@ T _C =25°C	80	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.56	°C/W



isc Silicon PNP Power Transistor**TIP34C****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -30\text{mA}; I_B = 0$	-80		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = -3\text{A}; I_B = -0.3\text{A}$		-1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -2.5\text{A}$		-4.0	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -4\text{V}$		-1.6	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	$I_C = -10\text{A}; V_{CE} = -4\text{V}$		-3.0	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}; I_B = 0$		-0.7	mA
I_{CES}	Collector Cutoff Current	$V_{CE} = -100\text{V}; V_{EB} = 0$		-0.4	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$		-1.0	mA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40		
h_{FE-2}	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	20	100	
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -10\text{V}; f_{test} = 1.0\text{MHz}$	3		MHz